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FORM PTO-1449  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT  DEC 0.5 2000					ATTY. DOCKET NO. ASMEX.186DV1		APPLICATION NO. 09/764,711			
					APPLICANT Raaijmakers et al.					
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				U.	S. PATENT DOCUMENTS					
XAMINER INITIAL	DOCUMENT NUMBER DATE			NAME		SUBCLASS	FILING DATE (IF APPROPRIATE			
42	1.	5,192,708	3/9/93	Beyer et al.		437	90	4/29/92		
1	2.	5,371,039	12/6/94	Ogar	о`	437	101 152 386	2/18/93 9/26/94 4/9/94		
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M	5. 6,297,088 B1 10/2/01 K		King	ing		243	1/2/00			
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				FOR	EIGN PATENT DOCUMENTS					
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DR	6.	6. Arienzo et al., "In Situ Arsenic-Doped Polysilicon for VLSI Applications" Transactions on Electron Devices								
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IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.